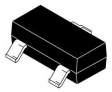
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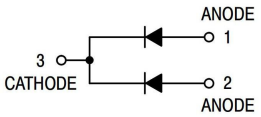
BAV70LT1G
Dual Switching Diode Common Cathode

Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant



SOT−23 (TO−236)



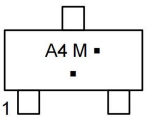
MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	V
Forward Current	I_F	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I_{FRM}	1.5	A
Non−Repetitive Peak Forward Current (Square Wave, T_J = 25°C prior to surge) t = 1 μs t = 10 μs t = 100 μs t = 1 ms t = 10 ms t = 100 ms	I_{FSM}	 31 16 10 4.5 2.5 1.0	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

MARKING DIAGRAM



A4 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

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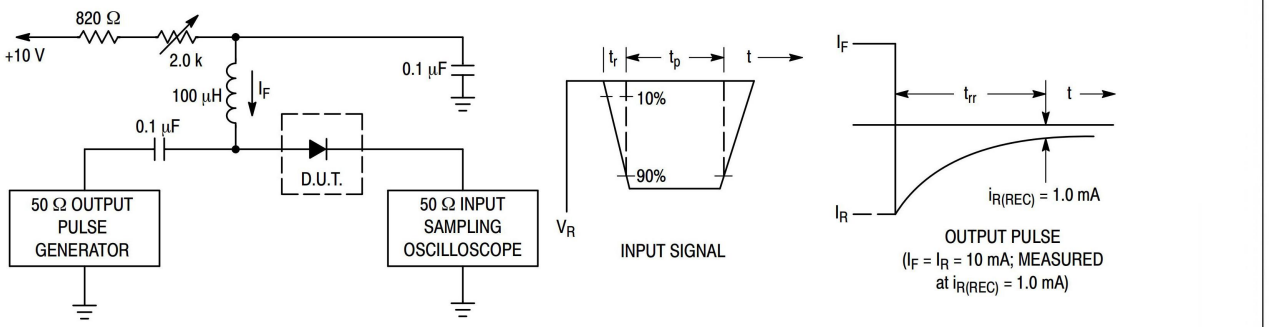
BAV70LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μA)	$V_{(BR)}$	100	–	V
Reverse Voltage Leakage Current (Note 3)	I_R			μA
(V_R = 25 V, T_J = 150°C)		–	60	
(V_R = 100 V)		–	1.0	
(V_R = 70 V, T_J = 150°C)		–	100	
Diode Capacitance (V_R = 0 V, f = 1.0 MHz)	C_D	–	1.5	pF
Forward Voltage	V_F			mV
(I_F = 1.0 mA)		–	715	
(I_F = 10 mA)		–	855	
(I_F = 50 mA)		–	1000	
(I_F = 150 mA)		–	1250	
Reverse Recovery Time R_L = 100 Ω (I_F = I_R = 10 mA, $I_{R(REC)}$ = 1.0 mA) (Figure 1)	t_{rr}	–	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while second diode is unbiased.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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Curves Applicable to Each Anode

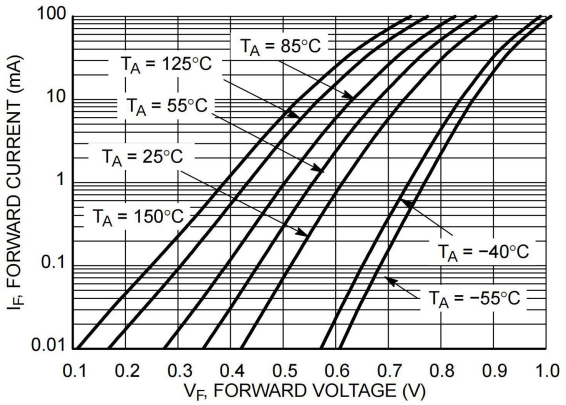


Figure 2. Forward Voltage

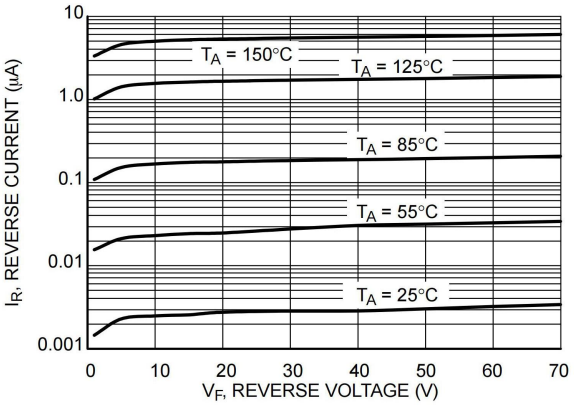


Figure 3. Leakage Current

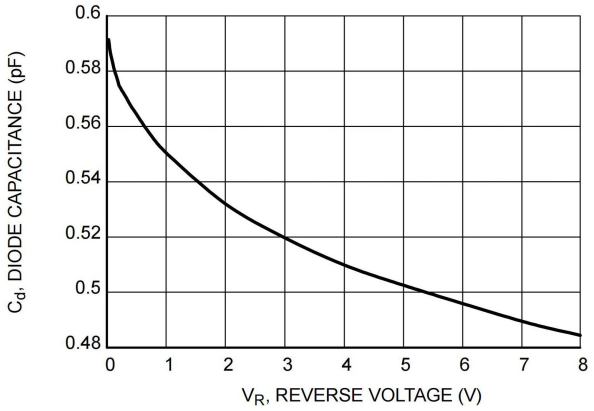


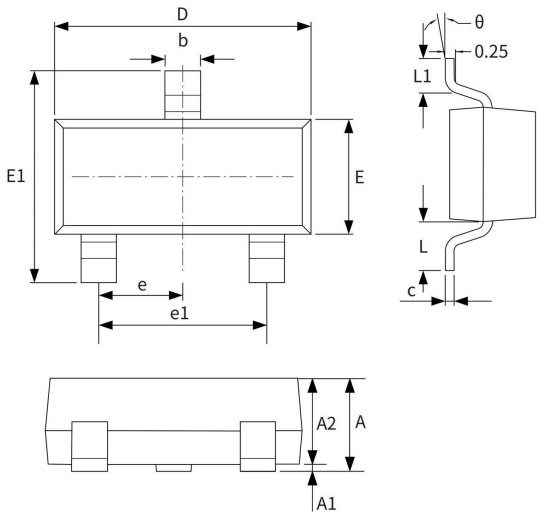
Figure 4. Capacitance

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Ordering Information

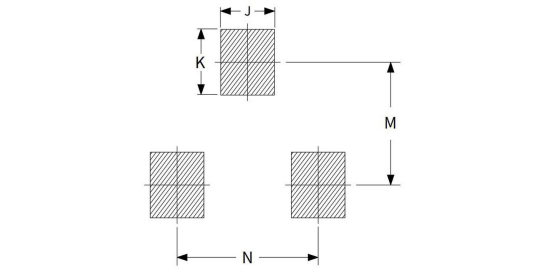
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077